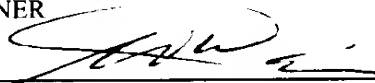


FORM PTO-1449		US Dept. of Commerce Patent and Trademark Office		ATTORNEY DOCKET NO. 410		SERIAL NO. 09/633,598	
INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)				APPLICANT Joan M. Redwing, et al.			
				FILING DATE August 7, 2000		GROUP TBA	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WSL	AA	5,192,987	3/1993	Khan, et al.			
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							X (abstract only)
OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)							
WSL	AE	M.D. McCluskey, N.M. Johnson, C.G. Van De Walle, D.P. Bour, M. Kneissl and W. Walukiewicz; Mat. Res. Soc. Symp. Proc. 521 (1998) , pg. 531					
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Continue on Page							
EXAMINER 					DATE CONSIDERED 8/20/01		
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